

Silicon PNP Power Transistors

2SB1362

DESCRIPTION

- With TO-3PN package
- Wide area of safe operation
- Complement to type 2SD2053

APPLICATIONS

- For high power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

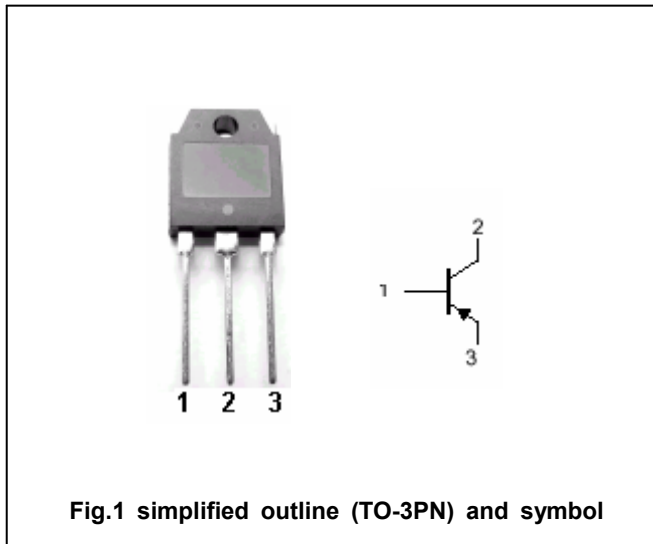


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-150	V
V _{CEO}	Collector-emitter voltage	Open base	-150	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current (DC)		-9	A
I _{CM}	Collector current -peak		-15	A
P _C	Collector power dissipation	T _C =25°C	100	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA; I _B =0	-150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-7A; I _B =-0.7A			-2.0	V
V _{BE}	Base-emitter on voltage	I _C =-7A; V _{CE} =-5V			-1.8	V
I _{CBO}	Collector cut-off current	V _{CB} =-150V; I _E =0			-50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-50	μA
h _{FE-1}	DC current gain	I _C =-20mA; V _{CE} =-5V	20			
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-5V	60		200	
h _{FE-3}	DC current gain	I _C =-7A; V _{CE} =-5V	15			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-5V		15		MHz
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =-10V		270		pF

◆ h_{FE-2} Classifications

Q	P
60-120	100-200

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PACKAGE OUTLINE

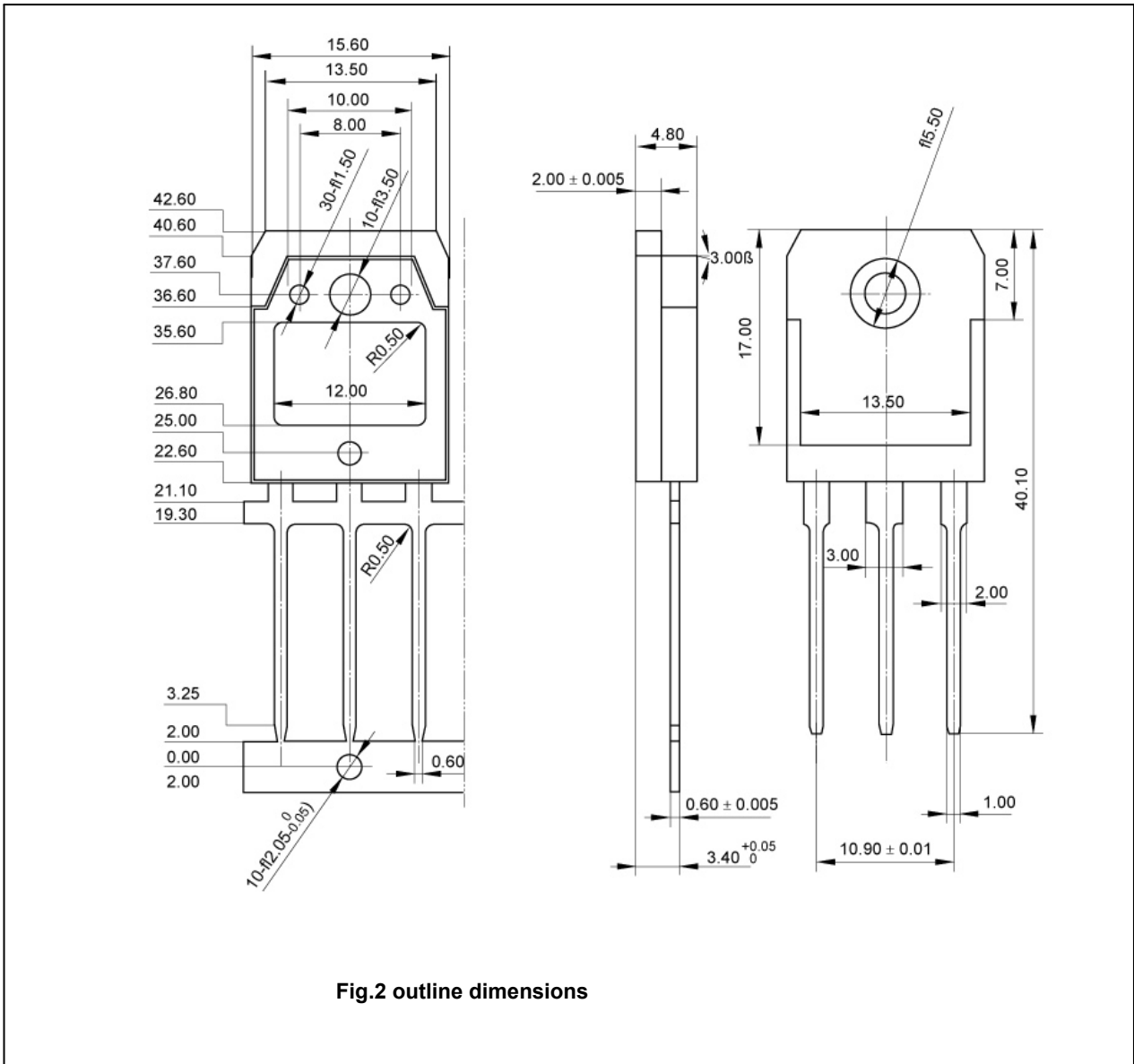


Fig.2 outline dimensions